

Extended InGaAs Photodiodes

GAP3000-2.05-TEC2-T08

Wavelength range

1200nm - 2200nm

Packages

TO-8

Applications

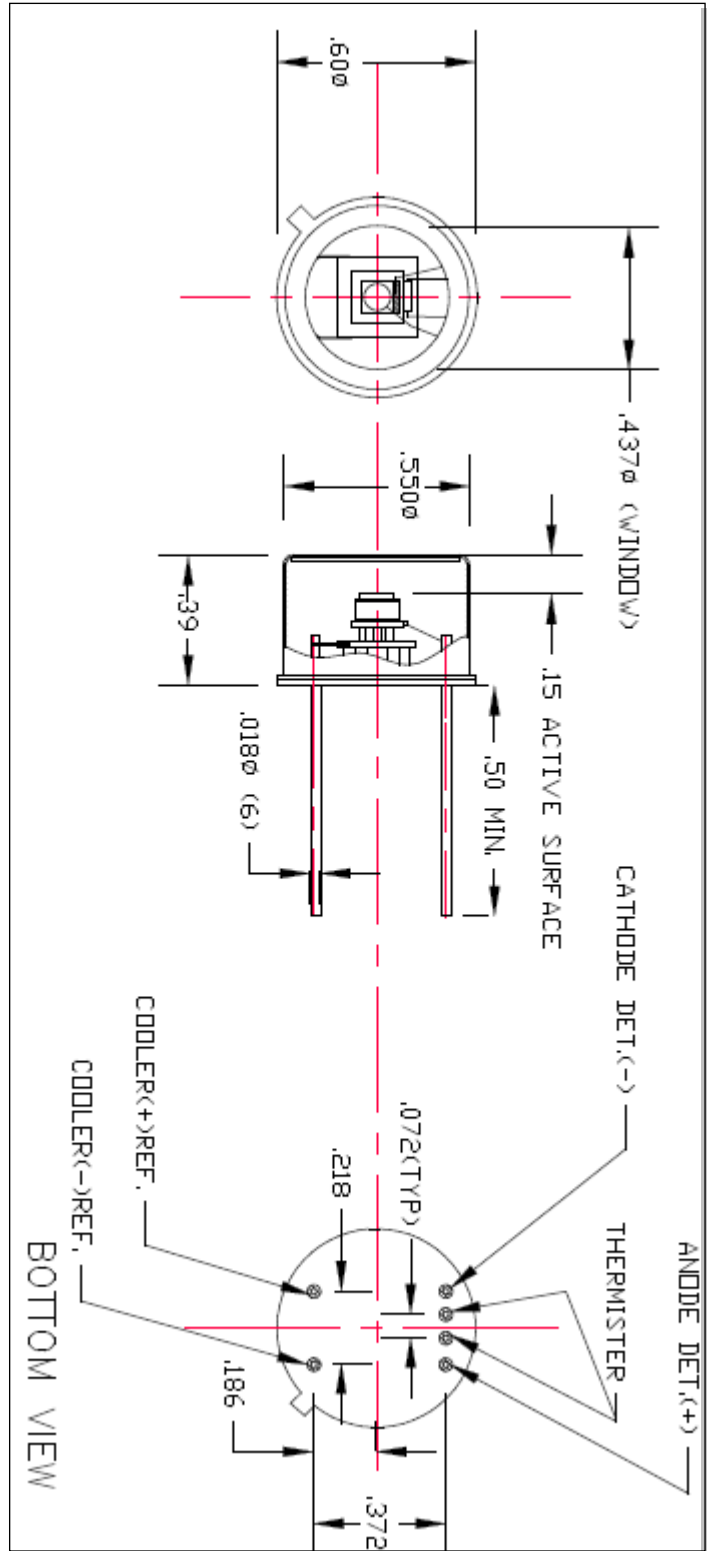
- Process monitoring
- Process analysis
- Infrared spectroscopy
- Optical power meters
- Temperature sensors
- Medical analysis

Features

- High responsivity
- High shunt resistance
- Low capacitance
- Planar design for high reliability

Technical Data

Conditions @ -10°C	Min.	Max.	Units
Cutoff Wavelength (50% of peak)	(Typ.) 2050		Nm
Active Area Diameter	1950	2050	µm
AR Coating Wavelength Band	1200	2200	Nm
@1300 nm	0.50	(Typ.) 0.60	A/W
@1550 nm	0.80	(Typ.) 0.90	A/W
@1900 nm	0.85	(Typ.) 1.0	A/W
VR = 0.5 V		20	nA
VR = 0 V		(Typ.) 8000	pF
VR = 10mV		(Typ.) 80	KΩ
-10°C		1.5	Volts
-10°C		1.3	Amps
R _{Th} @ T = 25°C		(Typ.) 1.1	KΩ
@ λ _P	(Typ. 3.0 E-13)		W/√Hz
50Ω-3dB, 0V	0.9		MHZ
Maximum Voltage Rating	0.5		Volts



TOLERANCES
ALL DIMS. ARE IN INCHES
XX PLACE DEC. \pm .010
XXX PLACE DEC. \pm .005
FRACTIONS \pm 1/64
ANGLES \pm 0.5°